



# FCC-hh electron cloud

L. Mether

I. Bellafont, E. Belli, G. Iadarola, R. Kersevan, K. Li, K. Ohmi, A. Romano, G. Rumolo, D. Schulte



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### Introduction

#### Main concerns of electron cloud

- Heat load and vacuum degradation due to electron flux on chamber wall
- Transverse instabilities due to interaction between beam and electron cloud
- Emittance growth, tune shift and spread, beam losses



# 13.2 mm + 15 mm -+

#### **Simulation studies**

Main chamber of beam screen (2015 version), Cu surface

Electron cloud build-up for 25 ns and 5 ns beam

- Arc dipoles, quadrupoles, drifts
- Effect of photoelectrons
- 12.5 ns bunch spacing
- Instability simulation studies

## Multipacting threshold

Secondary electron yield (SEY) limit for electron cloud build-up

	25 ns		5 ns	
	3.3 TeV	50 TeV	3.3 TeV	50 TeV
Dipole	1.7	1.7	1.6	1.5
Q-pole	1.3	1.4	1.2	1.2
Drift	1.9	1.9	1.6	1.5

5 ns beam more challenging than 25 ns

- SEY = 1.1 required to keep arcs e-cloud free
- $\rightarrow$  low-SEY surface treatment



Heat load scaled to device length in half-cell

Heat load due to e-cloud smaller than from synchrotron radiation

## Multipacting threshold

#### Secondary electron yield (SEY) limit for electron cloud build-up

	25 ns		5 ns		12.5 ns	
	3.3 TeV	50 TeV	3.3 TeV	50 TeV	3.3 TeV	50 TeV
Dipole	1.7	1.7	1.6	1.5	1.3	1.3
Q-pole	1.3	1.4	1.2	1.2	1.1	1.2
Drift	1.9	1.9	1.6	1.5	1.3	1.3

12.5 ns beam even more challenging than 5 ns beam

- At 3.3 TeV build-up in quadrupoles for SEY = 1.1
- $\rightarrow$  SEY ~ 1 required to keep arcs e-cloud free



Heat load scaled to device length in half-cell

#### Single bunch instability

Analytical estimate of threshold electron density for instability

With updated machine parameters

$$\rho_{e,th} = \frac{2\gamma\nu_s\omega_e\sigma_z/c}{\sqrt{3}KQr_0\beta L} \quad \text{with} \ \omega_e = \sqrt{\frac{\lambda_p r_e c^2}{\sigma_y(\sigma_x + \sigma_y)}}, \quad \begin{array}{c} K = \omega_e\sigma_z/c \\ Q = \min(\omega_e\sigma_z/c,7) \end{array} \qquad \begin{array}{c} \textbf{3.3 TeV} & \textbf{50 TeV} \\ \textbf{6 x 10^{10} m^{-3}} & \textbf{3.6 x 10^{11} m^{-3}} \end{array}$$

Above the multipacting threshold, central electron densities are in the instability regime



Central electron densities scaled to device length in half-cell

FCC Week 2017, Berlin

#### Effect of photoelectrons

Even with SEY = 1-1.1, electron densities can reach instability threshold due to photoelectrons

- depending on the number photons that reach the main chamber and the photoelectron yield
- For 5 ns and, especially, 12.5 ns the threshold is approached for  $N_e \simeq 1-5$  % of photon number

→ For up to 5% photons in main chamber (vacuum group estimate) yields > 0.2 problematic



Central electron densities scaled to device length in half-cell

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 $\rightarrow$  For up to 5% photons in main chamber (vacuum group estimate) yields > 0.2 problematic



In drifts, also electrons potentially produced in ante-chamber may move into main chamber and lead to increased electron density

ightarrow more detailed studies needed

Central electron densities scaled to device length in half-cell

#### Single bunch instability simulations

First instability simulation study: 25 ns beam at 3.3 TeV in dipole field – no stabilizing mechanisms



Ongoing studies:

- 5 ns at 3.3 TeV
- 25 ns at 50 TeV

→ seem to suggest similar scaling w.r.t. analytic estimate (TBC)

Over 17 000 turns (~ 5 s ): instability threshold around 1-2.5 x  $10^{11}$  m<sup>-3</sup>

• Compare to analytic estimate scaled to dipole length: 7.5 x 10<sup>10</sup> m<sup>-3</sup>

 $\rightarrow$  Analytic estimate slightly pessimistic, by factor 2-3

#### Stability at injection

Electron densities at 3.3 TeV much below instability threshold

• Due to smaller number of photons, and critical energy below Cu work function

	FCC	FCC Injection		
E [TeV]	50	1.5	3.3	5.5
E <sub>c</sub> [eV]	4030	0.11	1.14	5.26
N <sub>γ</sub> /p⁺m	0.0497	0.00149	0.00328	0.00546
$N_{eff}/N_{tot}$	0.878	6.1e-20	2.5e-3	0.108
N <sub>eff</sub> /p⁺m	0.0436	9.1e-23	8.2e-6	5.9e-3

Most critical case for stability may be at some intermediate energy



#### Conclusions

Low-SEY coating is needed for stability

Based on first results of single bunch instability simulations:

- Analytic threshold is slightly pessimistic, but correct order of magnitude
- Studies continuing: beam configurations, energy, arc elements and their combined effect, stabilizing mechanisms...

Enhanced electron densities due to photoelectrons at low SEY give some cause for concern

- Not extremely critical, but close enough that many details matter: surface properties, their accurate implementation in simulations, understanding of quantitative effect of model assumptions
  - Synergy with needs for LHC and HL-LHC

# Spares

Simulation parameters				
Bunch spacing [ns]	25	5		
Bunch intensity [p <sup>+</sup> ]	10 x 10 <sup>10</sup>	2 x 10 <sup>10</sup>		
Norm. emittance [m]	2.2e-6	0.44e-6		
Bunch length [m]	0.08			
Bunch train pattern	( 50 b + 12 e )*4	( 250 b + 60 e )*4		
	<b>Dipole</b> 16 T, L = 171.6 m			
Arc elements considered (FODO, L = 213.9 m)	<b>Quadrupole</b> 444 T/m, L = 12.6 m			
	<b>Drift</b> L = 26.6 m			



